

PHOTO-DIODE AND METHOD FOR FABRICATING THE SAME

ABSTRACT

Disclosed is a photodiode and a method for fabricating the same for reducing excessive electric field applied to a mesa-etched region, thereby providing a stable operation and a longer durability. The photodiode includes a substrate, a first conduction type buffer layer formed on the substrate, an amplifying layer having a superlattice structure formed on the first conduction type buffer layer to form a mesa structure, a second conduction type field controlling layer formed on the amplifying layer, a second conduction type ion injection layer formed within the field controlling layer, a second conduction type light-absorbing layer formed on the field controlling layer, a second conduction type buffer layer formed on the light-absorbing layer, and a first electrode and a second electrode formed to electrically contact the first conduction type buffer layer and the second conduction type buffer layer, respectively.

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